







OPA596

SBOSA42 – JUNE 2024

OPAx596 High-Voltage (85V), Low-Power (420μA), High-Slew Rate (100V/μs) Power Amplifier With Mux-Friendly Inputs

1 Features

- High slew rate: 100V/µs
- Low power consumption: 420µA
- · Wide power-supply range:
 - ±4V to ±42.5V
 - 8V to 85V
- · Mux-friendly inputs
- · Rail-to-rail input and out
- Gain bandwidth: 3.75MHz
- Low noise: 12.8nV/√Hz
- Low input bias current: 5pA
- High-output load drive: I_O ±30mA
- Wide temperature range: –40°C to +125°C
- · Industry-standard small packages:
 - DBV (5-pin SOT-23)
 - DGK (8-pin VSSOP)

2 Applications

- · Semiconductor test
- · LCD test
- · Programmable dc power supply
- CT and PET scanner
- · Source measurement unit (SMU)
- · Optical module
- · Lab and field Instrumentation

3 Description

The OPA596 and OPA2596 (OPAx596) are high-voltage (85V), high slew rate (100V/ μ s), micro-power (420 μ A), unity-gain stable operational amplifiers (op amps).

The OPAx596 enable the next generation of high-voltage systems, such as output load drivers in semiconductor test and digital power supplies by increasing the output voltage of the system though high-gain configurations. Low power consumption and industry-standard small packages allow the device to be used in high-density systems that are size constrained, while reducing the thermal management requirements for the system.

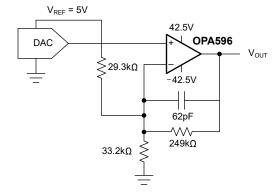
Through proprietary design techniques, the OPAx596 are capable of a very high slew rate with minimal power consumption to improve large-signal settling time and maximize the effective large-signal bandwidth. These devices also offers mux-friendly inputs that enable large differential voltage (up to 85V) and help improve settling behavior when compared to traditional inputs in multiplexed applications.

The OPAx596 are available in industry-standard packages and operates across the temperature range of –40°C to +125°C.

Device Information

PART NUMBER	CHANNELS	PACKAGE ⁽¹⁾
OPA596	Single	DBV (SOT-23, 5)
OPA2596 (2)	Dual	DGK (VSSOP, 8)

- (1) For more information, see Section 10.
- (2) Preview information



DAC Output Buffer With Gain



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4 Pin Configuration and Functions

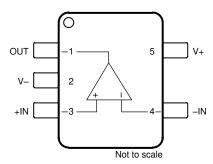


Figure 4-1. OPA596 DBV Package, 5-Pin SOT-23 (Top View)

Table 4-1. Pin Functions: OPA596

PIN	l	TYPE	DESCRIPTION			
NAME	NO.	1112	DESCRIF HON			
+IN	3	Input	Noninverting input			
-IN	4	Input	Inverting input			
OUT	1	Output	Output			
V+	5	Power	Positive (highest) power supply			
V-	2	Power	Negative (lowest) power supply			

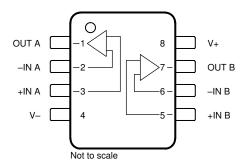


Figure 4-2. OPA2596 DGK Package, 8-Pin VSSOP (Top View)

Table 4-2. Pin Functions: OPA2596

PIN		TYPE	DESCRIPTION	
NAME	NO.	IIFE	DESCRIPTION	
+IN A	3	Input	Noninverting input, channel A	
+IN B	5	Input	Noninverting input, channel B	
–IN A	2	Input	nverting input, channel A	
–IN B	6	Input	nverting input, channel B	
OUT A	1	Output	Output, channel A	
OUT B	7	Output	Output, channel B	
V+	8	Power	Positive (highest) power supply	
V-	4	Power	Negative (lowest) power supply	



5 Specifications

5.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)(1)

			MIN I	/IAX	UNIT
	Supply voltage	Dual supply	±	±46.5	
V _S		Single supply, $V_S = (V+) - (V-)$		93	V
	Signal input his voltage(2)	Common-mode	(V-) - 0.3 (V+) +	0.3	V
	Signal input pin voltage ⁽²⁾	Differential	(V+) –	(V–)	V
	Input current, all pins ⁽²⁾	·		±10	mA
I _{SC}	Output short circuit ⁽³⁾		Continu	ious	
TJ	Junction temperature			150	°C
T _{STG}	Storage temperature		-65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.3V beyond the supply rails must be current-limited to 10mA or less.
- (3) Short-circuit to ground.

5.2 ESD Ratings

				VALUE	UNIT
V Clastrostatia diagharma	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±1500	V	
V (E	ESD)		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±500	\ \ \

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

			MIN	NOM MAX	UNIT
V	Supply voltage	Dual supply	±4	±42.5	· · · · · · · · · · · · · · · · · · ·
V _S		Single supply	8	85	V
T _A	Ambient temperature		-40	125	°C

5.4 Thermal Information

		OPA596	OPA2596	
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DGK (VSSOP)	UNIT
		5 PINS	8 PINS	1
R _{θJA}	Junction-to-ambient thermal resistance	165.4	143.6	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	99.1	50.4	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	64.5	78.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	42.6	3.0	°C/W
ΨЈВ	Junction-to-board characterization parameter	64.2	77.5	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

Product Folder Links: OPA596



5.5 Electrical Characteristics

 $at V_S = 85V (\pm 42.5V)$, $T_A = 25^{\circ}C$, $R_L = 10k\Omega$ to mid-supply, and $V_{CM} = V_{OUT} = mid$ -supply (unless otherwise noted)

	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET	VOLTAGE						
V _{OS}	Input offset voltage				±0.2	±1	mV
dV _{OS} /dT	Input offset voltage drift	T _A = -40°C to +125°C			±1	±6	μV/°C
PSRR	Power supply rejection ratio	8V ≤ V _S ≤ 85V			±1	±5	μV/V
INPUT BI	AS CURRENT		'				
					±5	±10	π Λ
I _B	Input bias current $T_A = -40^{\circ}\text{C to } +85^{\circ}$					±50	pА
		T _A = -40°C to +125°C				±1	nA
					±5	±10	π Λ
los	Input offset current	T _A = -40°C to +85°C				±50	рA
		T _A = -40°C to +125°C	_A = -40°C to +125°C			±1	nA
NOISE						'	
	Input voltage noise	f = 0.1Hz to 10Hz			1.4		μV _{PP}
		f = 100Hz			17.8		
e _n	Input voltage noise density	f = 1kHz			12.9		nV/√ Hz
	f = 10kHz				12.8		
in	Current noise density	f = 1kHz	f = 1kHz		10		fA/√ Hz
INPUT VO	DLTAGE		'				
V _{CM}	Common-mode voltage	Linear operation		(V-) - 0.1		(V+) - 3.5	V
OMED		44 > 44 > 654		126	140		ID.
CMRR	Common-mode rejection	$(V-) \le V_{CM} \le (V+) - 3.5V$	T _A = -40°C to +125°C	124	140		dB
INPUT IM	PEDANCE					'	
	Differential				100 2.5		MΩ pF
	Common-mode				10 5.5		GΩ pF
OPEN-LC	OOP GAIN						
		$(V-) + 1V < V_O < (V+) - 1.5V,$		134	140		
^	Onen leen veltege gein	$R_L = 10k\Omega$ to mid-supply	T _A = -40°C to +125°C	120	140		٩D
A _{OL}	Open-loop voltage gain	$(V-) + 3V < V_O < (V+) - 3.5V,$			126		dB
		$R_L = 2k\Omega$ to mid-supply	T _A = -40°C to +125°C		126		
FREQUE	NCY RESPONSE						
		G = 1			2.25		
GBW	Gain-bandwidth product	G = 10			3		MHz
		G = 100			3.75		
SR	Slew rate	G = ±1, V _O = 70V step			100		V/µs
ts	Settling time	To ±0.01%, G = -1, V _O = 10V	step, C _L = 100pF		2		μs
	Overload recovery	G = -1			115		ns
THD+N	Total harmonic distortion +	G = +1, V _O = 70V _{PP} , f = 1kHz	R _L = 10kΩ		-102		dB
אודטווו	noise	G - +1, v _O - /Uvpp, 1 = 1Km2	$R_L = 2k\Omega$		-95		uБ



5.5 Electrical Characteristics (continued)

at V_S = 85V (±42.5V), T_A = 25°C, R_L = 10k Ω to mid-supply, and V_{CM} = V_{OUT} = mid-supply (unless otherwise noted)

	PARAMETER TEST CONDITIONS			MIN	TYP	MAX	UNIT
ОИТРИТ	•					•	
		No load			12	50	mV
Vo	Voltage output swing from rail	$R_L = 10k\Omega$ to mid-supply			100	435	IIIV
	14	$R_L = 2k\Omega$ to mid-supply			500	2.05	V
I _{SC}	Output current				±30		mA
C _{LOAD}	Capacitive load drive				1		nF
Z _O	Open-loop output impedance				550		Ω
CURREN	NT LIMIT						
POWER	SUPPLY						
		1 - 0mA			420	490	
lQ	Quiescent current	$I_O = 0mA$	$T_A = -40^{\circ}\text{C to } +125^{\circ}\text{C}$			500	μA
TEMPER	RATURE					1	
	Overtemperature	Shutdown temperature Thermal hysteresis			185		°C
	shutdown				20		C

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6 Detailed Description

6.1 Overview

The OPAx596 are low power ($420\mu A$), high-slew rate ($100V/\mu s$), 85V operational amplifiers (op amps). These op amps uses a proprietary design technique to achieve a very high slew capability with minimal power consumption. The OPAx596 is capable of driving $\pm 30mA$ of output current and can swing to within 100mV of either power supply rail.

The amplifiers feature state-of-the-art CMOS technology and advanced design features that help achieve outstanding ac performance and enable small package options. The OPAx596 strengths also include 3.75MHz bandwidth, 12.8nV/√Hz noise spectral density, and low input bias current. These features make the OPAx596 an exceptional choice to gain or buffer the output of a digital-to-analog converter (DAC) in digitally programmable power supplies.

6.2 Functional Block Diagram

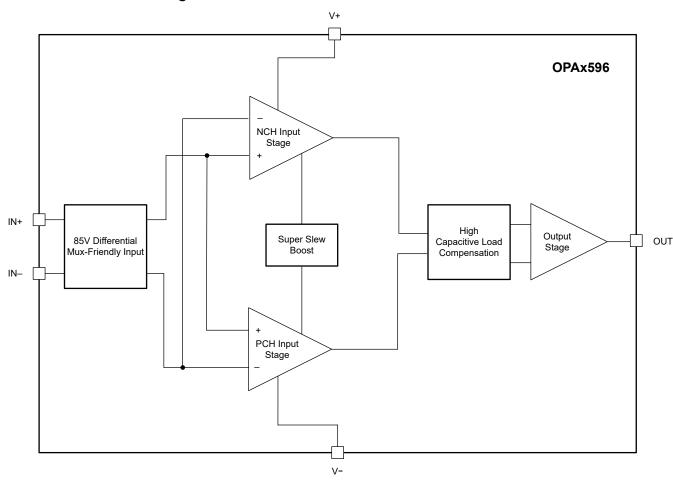


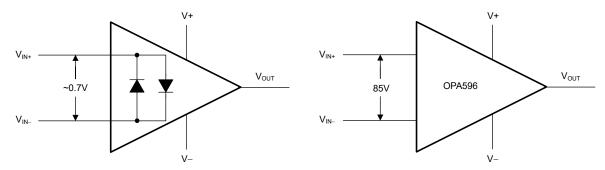
Figure 6-1. Functional Block Diagram



6.3 Feature Description

6.3.1 Mux-Friendly Inputs

The OPAx596 use a unique input architecture to eliminate the need for input protection diodes but still provide robust input protection under transient conditions. Conventional input diode protection schemes shown in Figure 6-2 can be activated by fast transient step responses and can introduce signal distortion and settling time delays because of alternate current paths, as shown in Figure 6-3. For low-gain circuits, these fast-ramping input signals forward-bias back-to-back diodes that cause an increase in input current and result in extended settling time.



Conventional Input Protection Limits Differential Input Range

OPA596 Provides Full 85V Differential Input Range

Figure 6-2. OPA596 Input Protection Does Not Limit Differential Input Capability

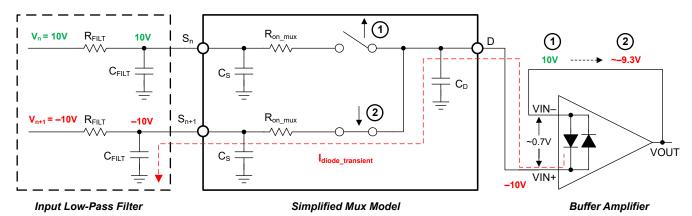


Figure 6-3. Back-to-Back Diodes Create Settling Issues

The OPAx596 feature a true high-impedance differential input capability for high-voltage applications. This patented input protection architecture does not introduce additional signal distortion or delayed settling time, making these devices an excellent choice for multichannel, high-switched, input applications. The OPAx596 tolerate a maximum differential swing (voltage between inverting and noninverting pins of the op amp) of up to 85V, making these devices a great choice for use as a comparator or in applications with fast-ramping or switched input signals.

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6.3.2 Thermal Protection

The OPAx596 has a thermal protection feature that prevents damage from self heating. When the junction temperature (T_J) reaches approximately 180°C, the op amp output stage disables. This thermal protection works by monitoring the temperature of the output stage and turning off the op amp output drive. Thermal protection forces the output to a high-impedance state. The OPAx596 is designed with approximately 30°C of thermal hysteresis and returns to normal operation when the output stage temperature becomes less than approximately 150°C.

This thermal protection is not designed to prevent this device from exceeding absolute maximum ratings, but rather from excessive thermal overload.

6.3.3 Slew Boost

Slew rate is the maximum rate of change of output voltage change with respect to time and is typically specified in units of volts per microsecond, V/µs. The OPAx596 can enter a slew condition when a large, rapid moving signal is applied at the input. While slewing, the op amp enters an open loop condition and significant slew induced distortion can be seen on the output signal.

Equation 1 shows that the slew rate of an op amp is typically determined by the saturation current of the input stage, I_{SAT} , and the compensation capacitor, C_C .

$$SR = \frac{I_{SAT}}{C_C} \tag{1}$$

The slew rate scales with the quiescent current, I_Q , of the op amp. There are several ways that designers have overcome slew rate limitation. For example, decompensation improves slew rate at the expense of stability by lowering C_C . More commonly, modern op amps are equipped with slew boost technology that increases I_{SAT} to overcome the inherent slew rate limitations. Slew boost circuits can vary in implementation, but designers can typically expect about a 4 × improvement over comparable unboosted op amps.

The OPAx596 uses a proprietary design to achieve an unprecedented slew rate to I_Q ratio. The novel slew boost technology in OPAx596 provides a nearly 100 × slew rate improvement over comparable unboosted op amps.

6.3.4 Overload Recovery

Overload recovery is defined as the time required for the op amp output to recover from a saturated state to a linear state. The output devices of the op amp enter a saturation region when the output voltage exceeds the rated operating voltage, either due to the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return back to the linear state. After the charge carriers return back to the linear state, the device begins to slew at the specified slew rate. Thus, the propagation delay in case of an overload condition is the sum of the overload recovery time and the slew time.

6.4 Device Functional Modes

The OPAx596 has a single functional mode and is operational when the power-supply voltage is between 8V (±4V) and 85V (±42.5V).



7 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

The OPAx596 are low power $(420\mu A)$, high-slew rate $(100V/\mu s)$, 85V power operational amplifiers (op amps). These op amps use a proprietary design technique to achieve a very high slewing capability while consuming minimal power. The low power consumption helps reduce heat generation on the board while the output swings near the supply rail. The high slew reduces slew related distortion at the output when dealing with large peak, high frequency signals.

7.2 Typical Applications

7.2.1 Bridge-Connected Piezoelectric Driver

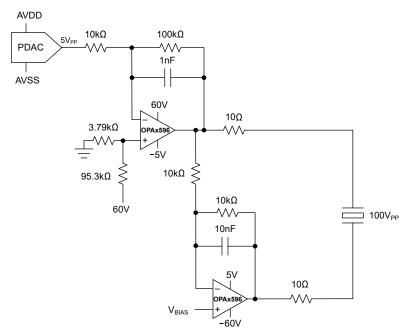


Figure 7-1. 100V_{PP} Piezoelectric Driver With Bridge Connected Load

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7.2.1.1 Design Requirements

The OPAx596 is used to drive a piezoelectric actuator with a 100V operating range at a frequency of 100Hz. The large capacitance inherent to the piezoelectric actuator can cause undesired ringing of the driver amplifier. An inaccurate response of the actuator is possible due in part to amplifier instability. Adequate phase margin for a 500nF equivalent load is necessary for a robust driver circuit for the piezoelectric actuator presented here.

Table 7-1. Design Parameters

VALUE
60V
-5V
500nF
0V to 100V
100Hz
5V _{PP}

7.2.1.2 Detailed Design Procedure

Piezoelectric actuators offer many benefits over traditional solenoid counterparts. Piezoelectric actuators are more precise, power efficient, and smaller in general when compared to solenoid actuators. One challenge with piezoelectric actuators is that the piezoelectric actuators operate over a very wide voltage range. Driving voltages of more than 60V are not uncommon, and can easily reach hundreds of volts. The OPAx596 operate with a supply voltage of up to 85V.

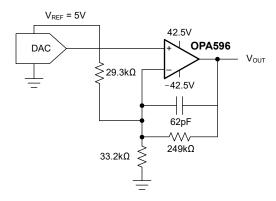
In this design example, the OPAx596 are used to provide a 100V_{PP} signal to control a high-voltage piezoelectric actuator (see also Figure 7-1). The piezoelectric actuator can be modeled as a large capacitor when operated at less than the resonant frequency. The piezoelectric actuator is treated as a floating load driven by two op amps of the OPAx596. The outputs of the op amps are set to be 180° out-of-phase to essentially double the voltage seen by the actuator load.

The signal voltage of the digital-to-analog converter is applied a 10V/V gain by the OPAx596. A simple voltage divider provides a 2.5V reference to level shift the output to create a unipolar driving voltage. An isolation resistor improves phase margin and stability. Add a small 10Ω R_{ISO} at the output of the OPAx596.

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7.2.2 DAC Output Gain and Buffer



7.2.2.1 Design Requirements

The OPAx596 is designed for use as an output driver stage with gain and provides a wide, bipolar supply voltage. Combined with the small size of the SOT23-5 package and the low power consumption, these features make this device a great choice for high-channel density systems, such as semiconductor test and manufacturing platforms where many channels are present. In this design example, the OPAx596 is configured for a gain of approximately 17V/V.

Table 7-2. Design Parameters

PARAMETER	VALUE
Supply voltage	-42.5V to +42.5V
Input voltage	0V to 5V
Output voltage	-42.5V to +42.5V
Gain	17V/V

7.2.2.2 Detailed Design Procedure

In this design example, the OPAx596 is configured as both a gain stage and output driver. The input signal to the amplifier is 0V to 5V, and the device is configured with a noninverting gain of 17V/V. The DAC reference voltage of 5V is used as a reference to enable a bipolar output swing. This configuration results in an output voltage of -42.5V to +42.5V. This design example is common in many systems that use a DAC to provide the input signal and require a wide output signal with low output current requirements. The OPAx596 can swing to either rail while remaining within the thermally specified limits. Such systems include test and measurement platforms and power supplies.

Product Folder Links: OPA596

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7.2.3 Single-Supply Piezoelectric Driver

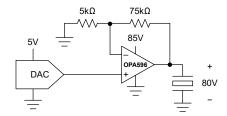


Figure 7-2. 80V Single-Supply Piezoelectric Driver

7.2.4 High-Side Current Sense

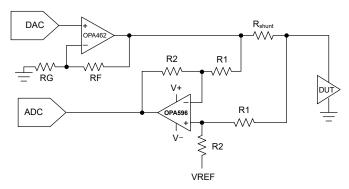


Figure 7-3. 100V High-Side Current Sense

7.2.5 High-Voltage Instrumentation Amplifier

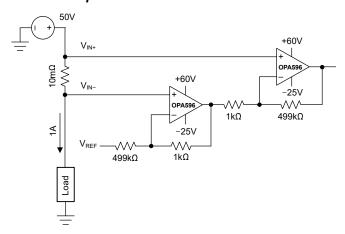


Figure 7-4. High-Voltage Instrumentation Amplifier

7.2.6 Composite Amplifier

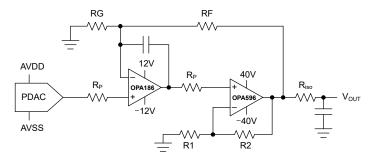


Figure 7-5. High-Precision, High-Voltage Output Composite Amplifier



7.3 Power Supply Recommendations

The OPAx596 operates from power supplies up to ±42.5V (85V), and as little as ±4V (8V) with excellent performance. Most behavior remains unchanged throughout the full operating voltage range. A power-supply bypass capacitor of at least 0.1µF is required for proper operation. Ensure that the capacitor voltage is rated for high voltage across the full operating temperature range. Some applications do not require an equal positive and negative output voltage swing. The OPAx596 can be powered with asymmetrical supplies.

7.4 Layout

7.4.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including the following guidelines:

- Noise can propagate into analog circuitry through the power pins of the op amp and the circuit as a
 whole. Connect low-ESR, 0.1µF ceramic bypass capacitors between each supply pin and ground. Place
 the capacitors as close to the device as possible. A single bypass capacitor from V+ to ground is sufficient for
 single supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most effective
 methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes.
 A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital
 and analog grounds paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If
 these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed
 to in parallel with the noisy trace.
- Place the external components as close to the device as possible.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Clean the PCB following board assembly for best performance.
- Any precision integrated circuit can experience performance shifts due to moisture ingress into the plastic
 package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to
 remove moisture introduced into the device packaging during the cleaning process. A low temperature, post
 cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

Product Folder Links: OPA596



7.4.1.1 Thermal Considerations

Through normal operation, the op amps can self-heat. Self-heating is a natural increase in the die junction temperature that occurs in every amplifier. This self-heating is a result of several factors, including quiescent power consumption, package thermal resistance, PCB layout, and device operating conditions.

Operate the OPAx596 within the rated junction temperature, T_J , range to avoid thermal shutdown. Use the Equation 2 to determine the estimated T_J

$$T_I = P_D \times \theta J_A + T_A \tag{2}$$

In a quiescent state, P_D is given by the product of the power supply and the quiescent current of the op amp. Equation 3 shows the calculation of T_J for the OPAx596 assuming an 85V power supply is used and an operating temperature of 25°C.

$$T_I = (85V \times 490\mu A) \times 165.4^{\circ} \frac{C}{W} + 25^{\circ} C$$
 (3)

$$T_{J} = 31.89^{\circ}C \tag{4}$$

The low power consumption of the OPAx596 causes minimal self-heating even in a small SOT23-5 package as given by Equation 4. In a loaded condition, P_D is equal to addition of the quiescent power, P_{DQ} and the power dissipated by the output stage, P_{DL} . The worst-case condition is given when the output voltage is equal to ½ of either supply rail (assuming symmetrical supplies, V+ and V-). In a worst-case condition, P_{DL} is given by Equation 5.

$$P_{DL} = \frac{\left(V + \right)^2}{4 \times R_I} \tag{5}$$

For example, assume the OPAx596 is powered with bipolar ± 42.5 V power supplies and drives a $5k\Omega$ load, R_L , to ground. The maximum increase in T_J is expected to be about 22°C as given by Equation 6. In this example, to keep the op amp within the *Absolute Maximum Ratings*, operate in T_A well under 128°C to account for different factors.

$$\Delta T_I = (41.7mW + 90.3mW) \times 165.4 \frac{^{\circ}C}{W}$$
 (6)



7.4.2 Layout Example

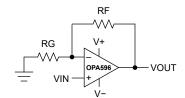


Figure 7-6. Schematic Representation of Noninverting Configuration

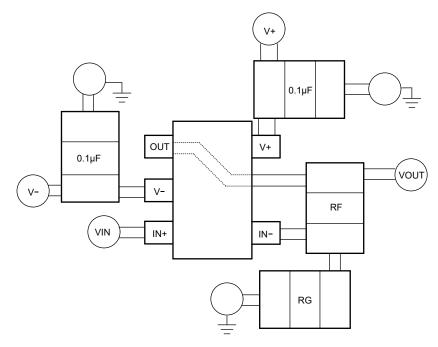


Figure 7-7. Board Layout for Noninverting Configuration of the SOT23-5 Package

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8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

8.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

8.3 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

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8.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

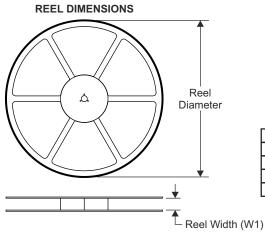
DATE	REVISION	NOTES
June 2024	*	Initial Release

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



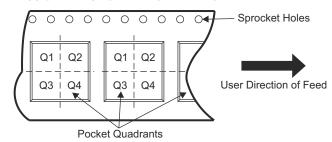
10.1 Tape and Reel Information



TAPE DIMENSIONS Ф B0 ▼ Ф

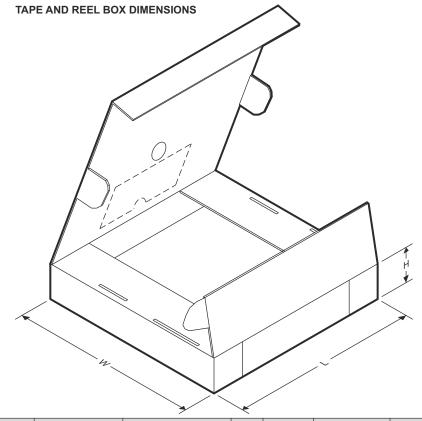
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers
	•

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA596DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
OPA596DBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3





Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA596DBVR	SOT-23	DBV	5	3000	213.0	191.0	35.0
OPA596DBVT	SOT-23	DBV	5	250	223.0	270.0	35.0

DBV0005A

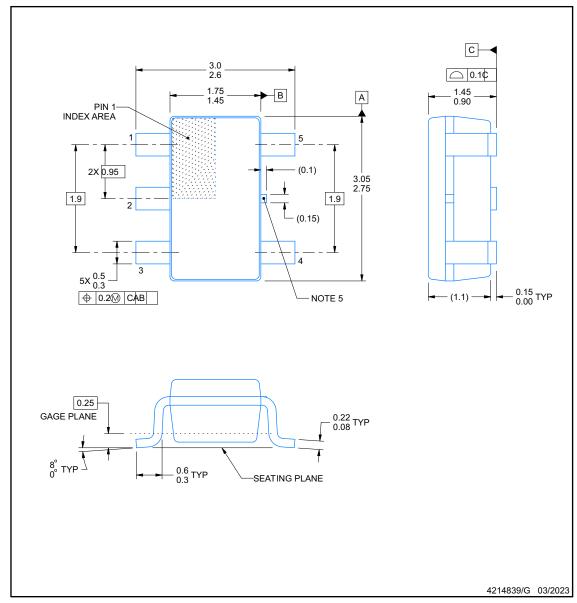




PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

- Reference JEDEC MO-178.
 Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
 Support pin may differ or may not be present.



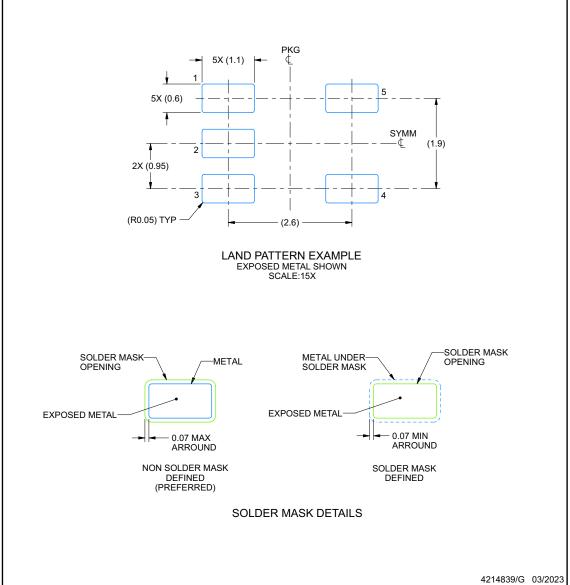


EXAMPLE BOARD LAYOUT

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR PKG 5X (1.1) 5X (0.6) SYMM (1.9)2X(0.95) (R0.05) TYP (2.6) SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL SCALE:15X

NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations
- design recommendations.

 9. Board assembly site may have different recommendations for stencil design.



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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
POPA596DBVR	ACTIVE	SOT-23	DBV	5	3000	TBD	Call TI	Call TI	-40 to 125		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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SMALL OUTLINE TRANSISTOR



NOTES:

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 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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